

# Franz J Tegude

## List of Publications by Year in descending order

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41  
papers

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#	ARTICLE	IF	CITATIONS
1	Tunneling-Related Leakage Currents in Coaxial GaAs/InGaP Nanowire Heterojunction Bipolar Transistors. <i>Physica Status Solidi (B): Basic Research</i> , 2021, 258, 2000395.	1.5	3
2	n-Doped InGaP Nanowire Shells in GaAs/InGaP Core-Shell Junctions. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900358.	1.5	3
3	A systematic study of Ga- and N-polar GaN nanowire-shell growth by metal organic vapor phase epitaxy. <i>CrystEngComm</i> , 2020, 22, 5522-5532.	2.6	7
4	Spatially controlled VLS epitaxy of gallium arsenide nanowires on gallium nitride layers. <i>CrystEngComm</i> , 2020, 22, 1239-1250.	2.6	5
5	Mask-less MOVPE of arrayed n-GaN nanowires on site- and polarity-controlled AlN/Si templates. <i>CrystEngComm</i> , 2019, 21, 7476-7488.	2.6	8
6	Germanium Template Assisted Integration of Gallium Arsenide Nanocrystals on Silicon: A Versatile Platform for Modern Optoelectronic Materials. <i>Advanced Optical Materials</i> , 2018, 6, 1701329.	7.3	0
7	Polarity- and Site-Controlled Metal Organic Vapor Phase Epitaxy of 3D GaN on Si(111). <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700485.	1.5	8
8	Toward Nanowire HBT: Reverse Current Reduction in Coaxial GaAs/InGaP n(i)p and n(i)pn Core-Multishell Nanowires. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 216, 1800562.	1.8	1
9	Electrical characterization and transport model of n-gallium nitride nanowires. <i>Applied Physics Letters</i> , 2015, 107, 082103.	3.3	3
10	High-Speed GaN/GaN Nanowire Array Light-Emitting Diode on Silicon(111). <i>Nano Letters</i> , 2015, 15, 2318-2323.	9.1	103
11	n-GaAs/InGaP/p-GaAs Core-Multishell Nanowire Diodes for Efficient Light-to-Current Conversion. <i>Advanced Functional Materials</i> , 2012, 22, 929-936.	14.9	56
12	n-Type Doping of Vapor-Liquid-Solid Grown GaAs Nanowires. <i>Nanoscale Research Letters</i> , 2011, 6, 65.	5.7	58
13	Axial pn-junctions formed by MOVPE using DEZn and TESn in vapor-liquid-solid grown GaAs nanowires. <i>Journal of Crystal Growth</i> , 2011, 315, 143-147.	1.5	33
14	Planar-defect characteristics and cross-sections of $\{001\}$ , $\{111\}$ , and $\{112\}$ InAs nanowires. <i>Journal of Applied Physics</i> , 2011, 109, 114320.	2.5	21
15	Ohmic contacts to n-GaAs nanowires. <i>Journal of Applied Physics</i> , 2011, 110, .	2.5	19
16	Optical properties of heavily doped GaAs nanowires and electroluminescent nanowire structures. <i>Nanotechnology</i> , 2011, 22, 085702.	2.6	29
17	High-Frequency Measurements on InAs Nanowire Field-Effect Transistors Using Coplanar Waveguide Contacts. <i>IEEE Nanotechnology Magazine</i> , 2010, 9, 432-437.	2.0	21
18	Controllable p-type doping of GaAs nanowires during vapor-liquid-solid growth. <i>Journal of Applied Physics</i> , 2009, 105, .	2.5	104

#	ARTICLE	IF	CITATIONS
19	Wavelength-selective receiver for simultaneous &#x03BB;=1.3 &#x00B5;m and &#x03BB;=1.55 &#x00B5;m RF optical transmission. , 2009, , .		0
20	On the temporal behavior of dc and rf characteristics of InAs nanowire MISFET. , 2009, , .		2
21	Monostable-Bistable Threshold Logic Elements in a fully complementary optical receiver circuit for high frequency applications. , 2008, , .		0
22	Large-Signal Performance of Resonant Tunnelling Diodes in K-Band Oscillators. , 2008, , .		1
23	Large-Signal Performance of Resonant Tunnelling Diodes in K-Band Oscillators. , 2008, , .		0
24	Sub-Nanosecond Pulse Generation using Resonant Tunneling Diodes for Impulse Radio. , 2007, , .		19
25	Single n-InAs Nanowire MIS-Field-Effect Transistor: Experimental and Simulation Results. , 2007, , .		2
26	Integrated InGaAs pin-diode on exactly oriented silicon (001) substrate suitable for 10 Gbit/s digital applications. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	4
27	InP-HEMT-TIA with Differential Optical Input Using Vertical High Topology Pin-Diodes. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	0
28	High performance III/V RTD and PIN diode on a silicon (001) substrate. Applied Physics A: Materials Science and Processing, 2007, 87, 539-544.	2.3	11
29	Low-Temperature DC and RF Measurement and Modelling of InGaAs-InAlAs Resonant Tunneling Diodes down to 15 K. , 2006, , .		2
30	Single InGaAs nanowhiskers characterized by analytical transmission electron microscopy. Phase Transitions, 2006, 79, 727-737.	1.3	6
31	Comparison of the passivation effects on self- and non-self-aligned InP/InGaAs/InP double heterostructure bipolar transistors by low-temperature deposited SiNx. Journal of Applied Physics, 2004, 96, 777-783.	2.5	9
32	Surface Recombination Mechanism in Graded-Base InGaAs-InP HBTs. IEEE Transactions on Electron Devices, 2004, 51, 1044-1045.	3.0	18
33	Effects of (NH <sub>4</sub> ) <sub>2</sub> S passivation on the performance of graded-base InGaAs/InP HBTs. Physica Status Solidi A, 2004, 201, 1017-1021.	1.7	11
34	Different approaches for integrating HBTs and EAMs. , 0, , .		0
35	Buffer optimization for INP-ON-SI [001] quasi-substrates. , 0, , .		2
36	Manufacturability and electrical characteristics of Si/SiGe interband tunnelling diodes. , 0, , .		0

#	ARTICLE	IF	CITATIONS
37	Characterisation of GaAs nanowhiskers grown on GaAs and Si substrates. , 0, , .		3
38	Optimizing lateral HBT design by utilizing performance estimations. , 0, , .		0
39	Fabrication of transferred-substrate HBT with simple technology. , 0, , .		0
40	High-speed InP-based resonant tunnelling diode on silicon substrate. , 0, , .		2
41	Fabrication and Electrical Characterisation of n-InAs Single Nanowhisker Field-Effect Transistors. , 0, , .		1